## NSN 5962-01-355-3768

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View Online at https://aerobasegroup.com/nsn/5962-01-355-3768

Body Length:
1.490 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
1.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Burn in and electrostatic sensitive and monolithic and programmed and bipolar
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Complementary-metal oxide-semiconductor logic
Input Circuit Pattern:
23 input
Case Outline Source And Designator:
D-10 mil-m-38510
Current Rating Per Characteristic:
80.00 milliamperes forward current, nonrepetitive, peak total value minor
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
-0.3 volts power source and 6.25 volts power source
Time Rating Per Chacteristic:
200.00 nanoseconds access
Memory Device Type:
Eeprom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.)
Terminal Type And Quantity:
28 printed circuit
Shelf Life:
N/a
Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

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